**Product data sheet** 

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Logic level compatible
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- AEC-Q101 qualified

## 3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

| Symbol            | Parameter                        | Conditions  |     | Min | Тур | Max | Unit |  |
|-------------------|----------------------------------|---|-----|-----|-----|-----|------|--|
| $V_{DS}$          | drain-source voltage             | T <sub>j</sub> = 25 °C  |     | -   | -   | 60  | V    |  |
| V <sub>GS</sub>   | gate-source voltage              |   |     | -20 | -   | 20  | V    |  |
| I <sub>D</sub>    | drain current                    | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C                        | [1] | -   | -   | 1.5 | Α    |  |
| Static characte   | Static characteristics           |   |     |     |     |     |      |  |
| R <sub>DSon</sub> | drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 1.5 \text{ A}; T_j = 25 ^{\circ}\text{C}$ |     | -   | 176 | 222 | mΩ   |  |

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



# 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline      | Graphic symbol |
|-----|--------|-------------|-------------------------|----------------|
| 1   | G      | gate        | 3                       | D<br>I         |
| 2   | S      | source      |                         |                |
| 3   | D      | drain       | 1 2<br>TO-236AB (SOT23) | G S 017aaa255  |

# 6. Ordering information

Table 3. Ordering information

| Type number | Package  |  |         |  |  |  |
|-------------|----------|--|---------|--|--|--|
|             | Name     | Description                              | Version |  |  |  |
| PMV230ENEA  | TO-236AB | plastic surface-mounted package; 3 leads | SOT23   |  |  |  |

# 7. Marking

Table 4. Marking codes

|            | Marking code [1] |
|------------|------------------|
| PMV230ENEA | DY%              |

[1] % = placeholder for manufacturing site code

# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol               | Parameter                                    | Conditions  |     | Min | Max  | Unit |
|----------------------|--|---|-----|-----|------|------|
| $V_{DS}$             | drain-source voltage                         | T <sub>j</sub> = 25 °C  |     | -   | 60   | V    |
| $V_{GS}$             | gate-source voltage                          |   |     | -20 | 20   | V    |
| I <sub>D</sub>       | drain current                                | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C                    | [1] | -   | 1.5  | Α    |
|                      |  | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C                   | [1] | -   | 0.9  | Α    |
| I <sub>DM</sub>      | peak drain current                           | $T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$                 |     | -   | 5.9  | Α    |
| E <sub>DS(AL)S</sub> | non-repetitive drain-source avalanche energy | $T_{j(init)}$ = 25 °C; $I_D$ = 0.14 A; DUT in avalanche (unclamped) |     | -   | 6    | mJ   |
| P <sub>tot</sub>     | total power dissipation                      | T <sub>amb</sub> = 25 °C  | [2] | -   | 480  | mW   |
|                      |  |   | [1] | -   | 950  | mW   |
|                      |  | T <sub>sp</sub> = 25 °C   |     | -   | 1.45 | W    |
| Tj                   | junction temperature                         |   |     | -55 | 150  | °C   |
| T <sub>amb</sub>     | ambient temperature                          |   |     | -55 | 150  | °C   |
| T <sub>stg</sub>     | storage temperature                          |   |     | -65 | 150  | °C   |
| Source-dra           | in diode                                     |   |     | '   |      |      |
| Is                   | source current                               | T <sub>amb</sub> = 25 °C  | [1] | -   | 0.8  | Α    |
| ESD maxim            | num rating                                   |   | '   |     | '    | ,    |
| V <sub>ESD</sub>     | electrostatic discharge voltage              | НВМ   | [3] | -   | 2000 | V    |

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

<sup>[2]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

<sup>[3]</sup> Measured between all pins.

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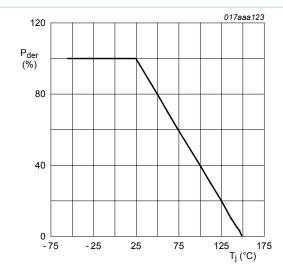


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

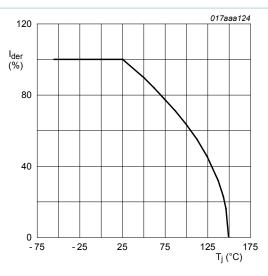


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

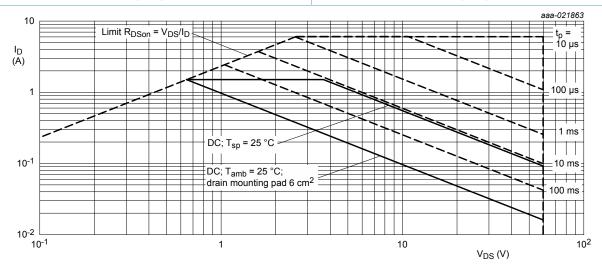


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

## 9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol                | Parameter  | Conditions  |     | Min | Тур | Max | Unit |
|-----------------------|--|-------------|-----|-----|-----|-----|------|
| R <sub>th(j-a)</sub>  | thermal resistance from junction to ambient      | in free air | [1] | -   | 227 | 261 | K/W  |
|                       |  |             | [2] | -   | 114 | 131 | K/W  |
| R <sub>th(j-sp)</sub> | thermal resistance from junction to solder point |             |     | -   | 20  | 23  | K/W  |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

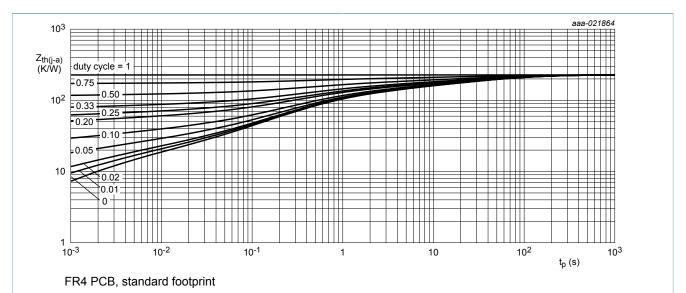


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

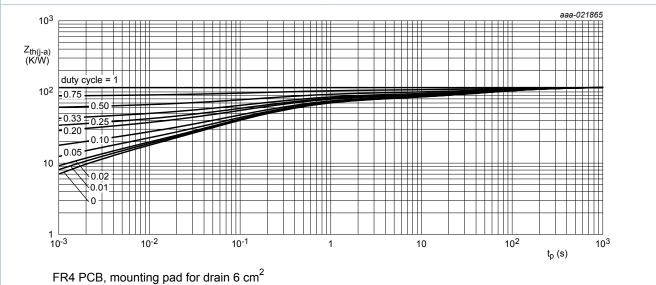


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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PMV230ENEA

## 10. Characteristics

Table 7 Characteristics

| Symbol              | Parameter                         | Conditions  | Min | Тур  | Max | Unit |
|---------------------|-----------------------------------|---|-----|------|-----|------|
| Static chara        | acteristics                       |   |     |      |     | _    |
| $V_{(BR)DSS}$       | drain-source<br>breakdown voltage | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$                            | 60  | -    | -   | V    |
| $V_{GSth}$          | gate-source threshold voltage     | $I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$                 | 1.3 | 1.7  | 2.7 | V    |
| I <sub>DSS</sub>    | drain leakage current             | V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C   | -   | -    | 1   | μA   |
| I <sub>GSS</sub>    | gate leakage current              | V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C   | -   | -    | 10  | μA   |
|                     |                                   | V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C  | -   | -    | -10 | μA   |
|                     |                                   | V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C   | -   | -    | 1   | μA   |
|                     |                                   | V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C  | -   | -    | -1  | μA   |
| R <sub>DSon</sub>   | drain-source on-state             | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 1.5 A; T <sub>j</sub> = 25 °C  | -   | 176  | 222 | mΩ   |
| res                 | resistance                        | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 1.5 A; T <sub>j</sub> = 150 °C | -   | 332  | 441 | mΩ   |
|                     |                                   | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 1.4 A; T <sub>j</sub> = 25 °C | -   | 196  | 262 | mΩ   |
| 9 <sub>fs</sub>     | forward transconductance          | $V_{DS}$ = 10 V; $I_{D}$ = 1.5 A; $T_{j}$ = 25 °C                       | -   | 6.2  | -   | S    |
| $R_G$               | gate resistance                   | f = 1 MHz   | -   | 9.3  | -   | Ω    |
| Dynamic ch          | naracteristics                    |   | ,   |      | '   |      |
| Q <sub>G(tot)</sub> | total gate charge                 | $V_{DS} = 30 \text{ V}; I_D = 1.5 \text{ A}; V_{GS} = 10 \text{ V};$    | -   | 3.9  | 4.8 | nC   |
| $Q_{GS}$            | gate-source charge                | T <sub>j</sub> = 25 °C  | -   | 0.4  | -   | nC   |
| $Q_{GD}$            | gate-drain charge                 |   | -   | 0.7  | -   | nC   |
| C <sub>iss</sub>    | input capacitance                 | $V_{DS} = 30 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$       | -   | 177  | -   | pF   |
| C <sub>oss</sub>    | output capacitance                | T <sub>j</sub> = 25 °C  | -   | 15   | -   | pF   |
| C <sub>rss</sub>    | reverse transfer capacitance      |   | -   | 10.6 | -   | pF   |
| t <sub>d(on)</sub>  | turn-on delay time                | $V_{DS} = 30 \text{ V}; I_D = 1.5 \text{ A}; V_{GS} = 10 \text{ V};$    | -   | 6.3  | -   | ns   |
| t <sub>r</sub>      | rise time                         | $R_{G(ext)} = 6 \Omega$ ; $T_j = 25 °C$                                 | -   | 8.2  | -   | ns   |
| t <sub>d(off)</sub> | turn-off delay time               |   | -   | 13   | -   | ns   |
| t <sub>f</sub>      | fall time                         |   | -   | 4.6  | -   | ns   |
| Source-dra          | in diode                          |   | I   |      | 1   |      |
| $V_{SD}$            | source-drain voltage              | I <sub>S</sub> = 0.8 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C   | -   | 0.8  | 1.2 | V    |

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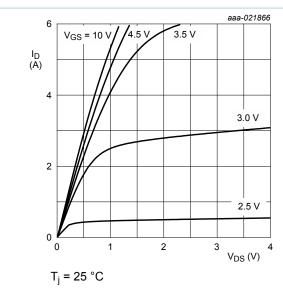


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

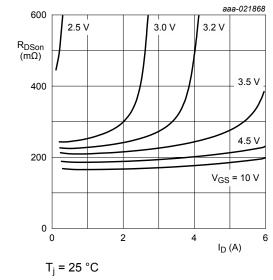


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

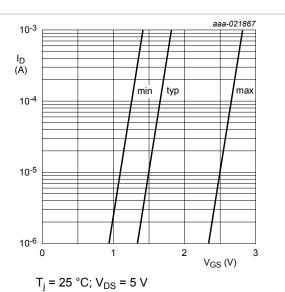


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

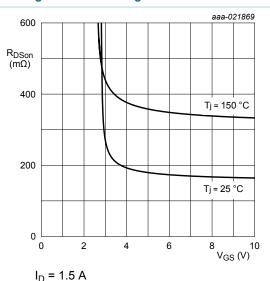


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

### **60V, N-channel Trench MOSFET**

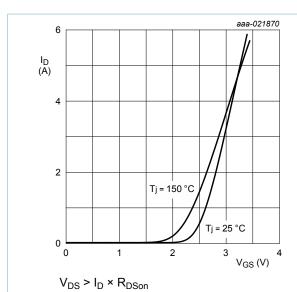


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

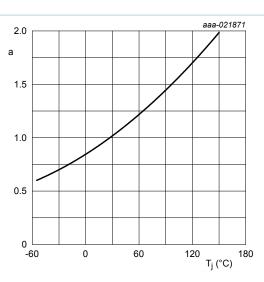


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

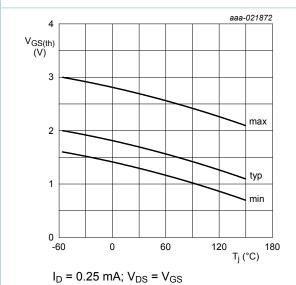
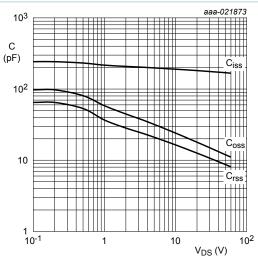


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

### 60V, N-channel Trench MOSFET

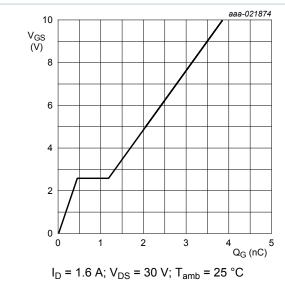


Fig. 14. Gate-source voltage as a function of gate charge; typical values

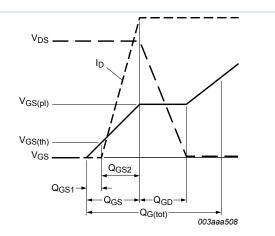


Fig. 15. MOSFET transistor: Gate charge waveform definitions

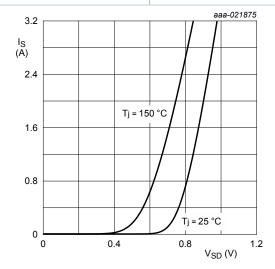
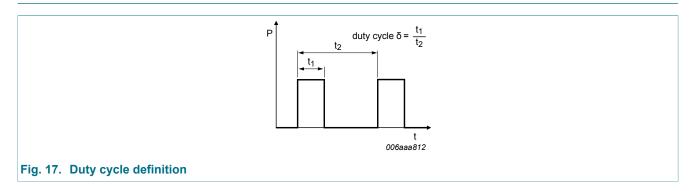


Fig. 16. Source current as a function of source-drain voltage; typical values

 $V_{GS} = 0 V$ 

**60V, N-channel Trench MOSFET** 

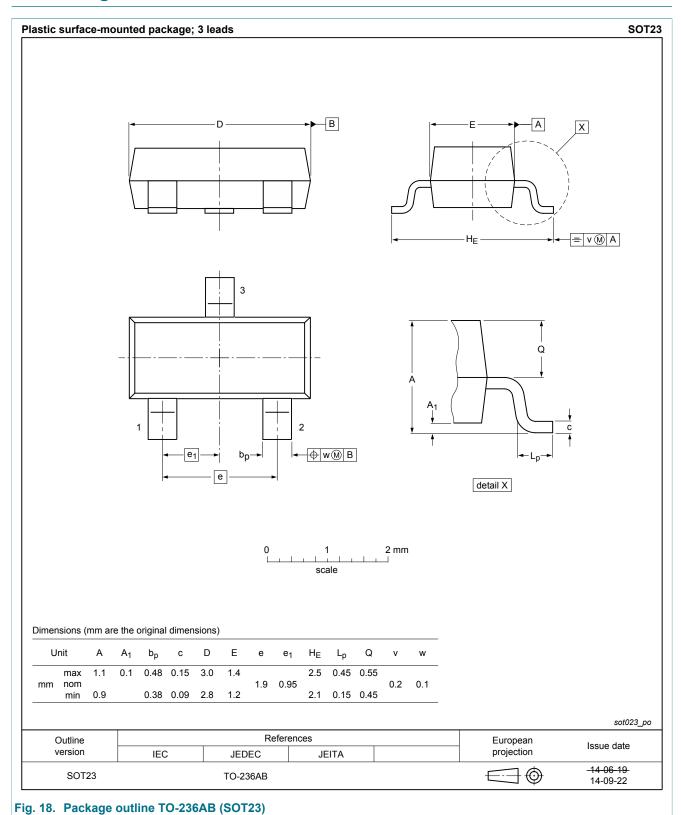
## 11. Test information



# 11.1 Quality information

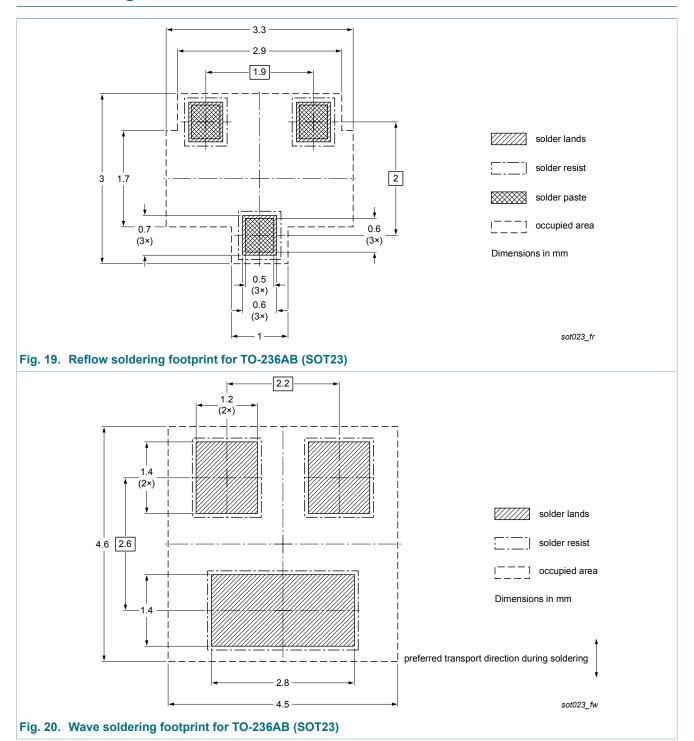
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

# 12. Package outline



**60V, N-channel Trench MOSFET** 

# 13. Soldering



**60V, N-channel Trench MOSFET** 

# 14. Revision history

### Table 8. Revision history

| Data sheet ID  | Release date | Data sheet status  | Change notice | Supersedes |
|----------------|--------------|--------------------|---------------|------------|
| PMV230ENEA v.1 | 20160302     | Product data sheet | -             | -          |

#### 60V, N-channel Trench MOSFET

## 15. Legal information

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|--------------------------------------|--------------------|---|
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PMV230ENEA

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**60V, N-channel Trench MOSFET** 

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# **PMV230ENEA**

### **60V, N-channel Trench MOSFET**

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